PATENT ABSTRACTS OF JAPAN

(11)Publication number:

2004-012513

(43) Date of publication of application: 15.01.2004

(51)Int.Cl.

G03F 7/004 H01L 21/027

(21)Application number: 2002-161651

(71)Applicant: MATSUSHITA ELECTRIC IND CO LTD

(22)Date of filing:

03.06.2002

(72)Inventor: ENDO MASATAKA

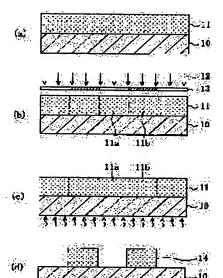
SASAKO MASARU

(54) METHOD OF FORMING PATTERN

(57)Abstract:

PROBLEM TO BE SOLVED: To decrease an edge roughness of lines in a resist pattern obtained by irradiation with electron beams at a low acceleration voltage.

SOLUTION: A resist film 11 consisting of a chemically amplifying resist material having an acid generating agent containing nonaflüorobutane sulfonic acid as an anion is formed. The resist film 11 is selectively irradiated with electron beams at a ≤10 kV low acceleration voltage for pattern exposure and then developed to form a resist pattern 14.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]